ECEN689: Special Topics in Optical Interconnects Circuits and Systems Spring 2022

Lecture 1: Introduction



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Analog & Mixed-Signal Center
Texas A&M University

Announcements

 Homework 1 is posted on website and due Jan 25

Class Topics

- System and design issues relevant to high-speed optical interconnects
- Channel properties
 - Modeling, measurements, communication techniques
- Optical interconnect circuits
 - Drivers, receivers, equalizers, timing systems
- Optical interconnect system design
 - Modeling and performance metrics
- Optical interconnect system examples

Administrative

Instructor:

- Sam Palermo
- 315E WERC Bldg., 979-458-4114, spalermo@tamu.edu
- Office hours: M 10:00AM-11:30AM & F 1:00PM-2:30PM
 - Online via Zoom
- Lectures: TR 5:30PM-6:46PM, ZACH 361
- Class web page
 - https://people.engr.tamu.edu/spalermo/ecen689 oi.html

Class Material

- Textbook: Class Notes and Technical Papers
- Key References
 - Broadband Circuits for Optical Fiber Communication, E. Sackinger, Wiley, 2005.
 - http://onlinelibrary.wiley.com/book/10.1002/0471726400
 - Design of Integrated Circuits for Optical Communications, B. Razavi, McGraw-Hill, 2003.
 - Advanced Signal Integrity for High-Speed Digital Designs, S. H. Hall and H. L. Heck, John Wiley & Sons, 2009.
 - High-Speed Digital Design: A Handbook of Black Magic, H. Johnson & M. Graham, Prentice Hall, 1993.
- Class notes will be posted on the web

Grading

- Exams (50%)
 - Two midterm exams (25% each)
- Homework (25%)
 - Collaboration is allowed, but independent simulations and write-ups
 - Need to setup CADENCE simulation environment
 - Turn in via Canvas
 - No late homework will be graded
- Final Project (25%)
 - Groups of 1-3 students
 - Report and PowerPoint presentation required
 - Turn in report and presentation files via Canvas

Prerequisites

- This is a circuits & systems & photonics class
- Circuits
 - ECEN474/704 or approval of instructor
 - Basic knowledge of CMOS gates, flops, etc...
 - Circuit simulation experience (HSPICE, Spectre)
- Systems
 - Basic knowledge of s- and z-transforms
 - Basic digital communication knowledge
 - MATLAB experience
- If you are strong in photonics, but weak in the above areas, then the assignments can be adjusted for more of a photonics emphasis

Simulation Tools

- Matlab
- ADS (Statistical BER link analysis)
- Cadence
- 90nm CMOS device models
 - Can use other technology models if they are a 90nm or more advanced CMOS node
- Other tools, schematic, layout, etc... are optional

Preliminary Schedule

	Topic	Week
I.	Optical Channel Properties	Week 1-8
II.	Optical Devices	
III.	Receiver Analysis	
IV.	Receiver Circuits	
	1 st MIDTERM	Mar. 10
V.	Transmitter Analysis	
VI.	Transmitter Circuits	Week 9-14
VII.	Laser Sources	
VIII.	RF Photonics & Photonic NoCs	
	2 nd MIDTERM	Apr. 28
	Project Report Due	May 3
	Project Presentations	May 10 (3:30PM-5:30PM)

^{*}Exam dates are approximate and subject to change with reasonable notice.

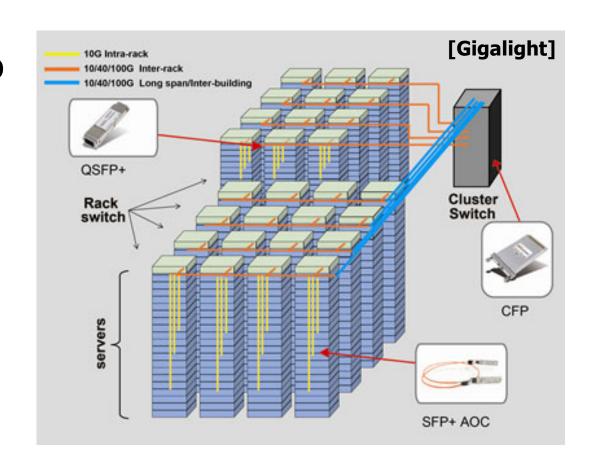
Dates may change with reasonable notice

Optical Interconnects

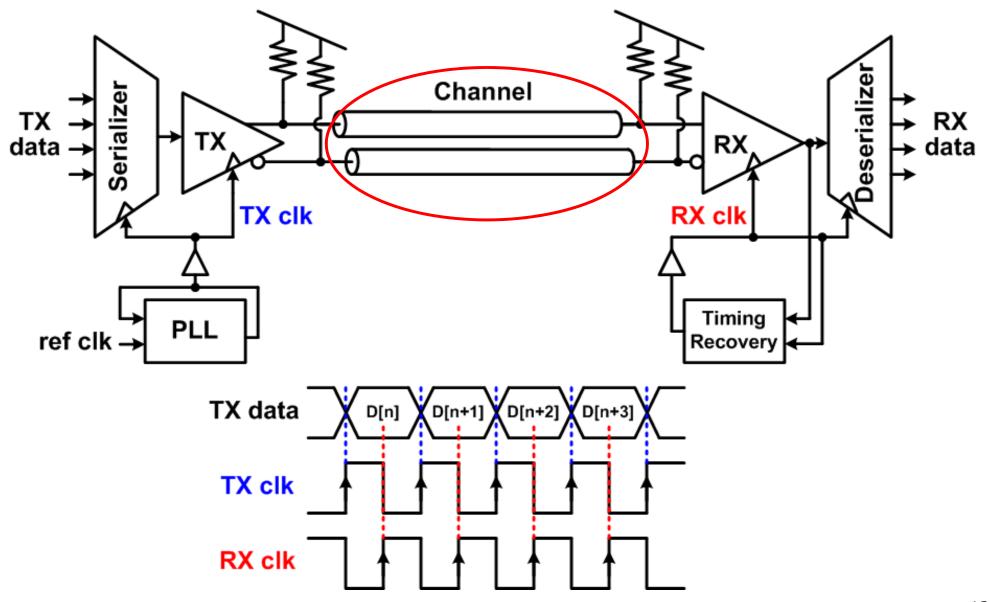
- Electrical Channel Issues
- Optical Channel
- Optical Transmitter Technology
- Optical Receiver Technology
- Optical Integration Approaches

Data Center Links

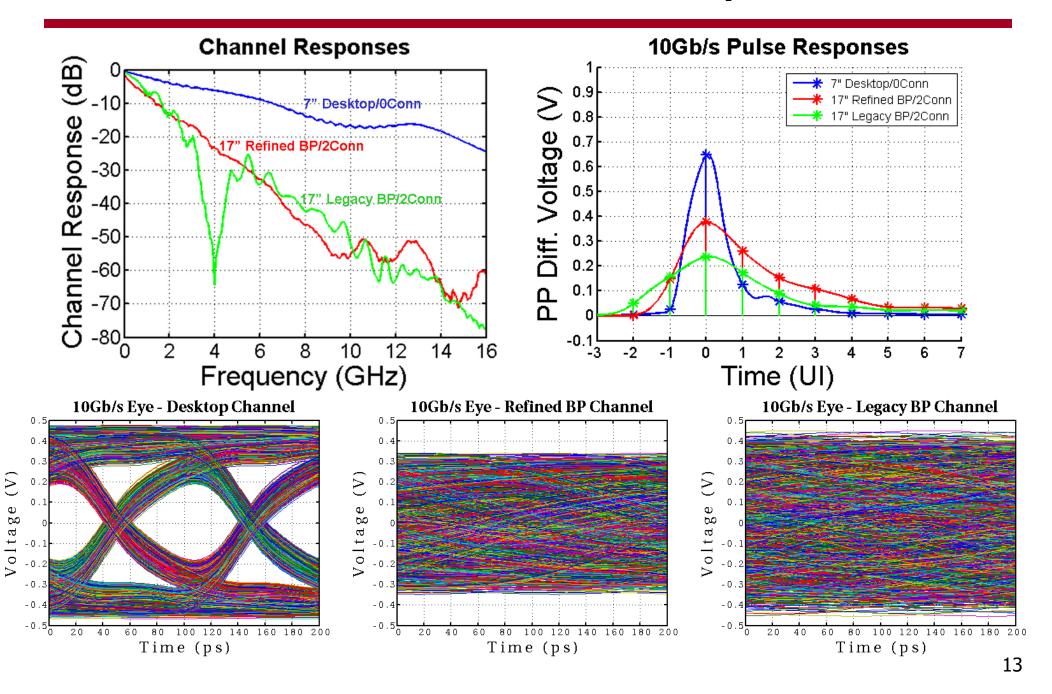
- Different interconnect technologies are used to span various distances
- Electrical I/O
 - Chip-to-module
 - Intra-rack (DAC cables)
- Optical I/O
 - Intra-rack (AO cables)
 - TOR switch to edge switch



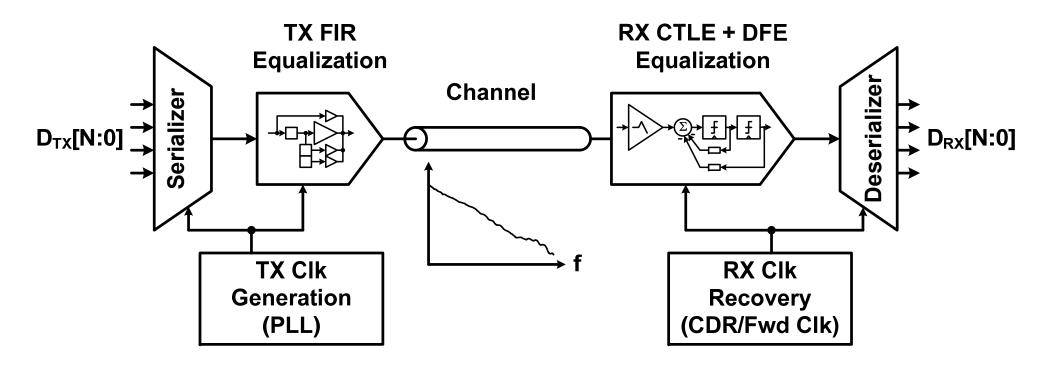
High-Speed Electrical Link System



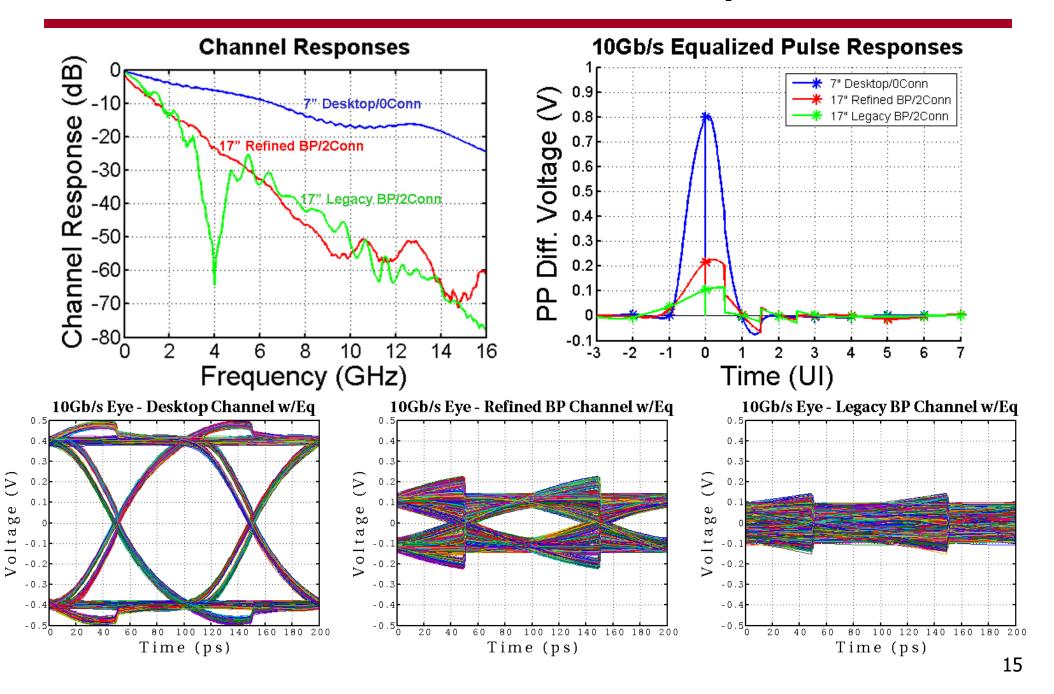
Channel Performance Impact



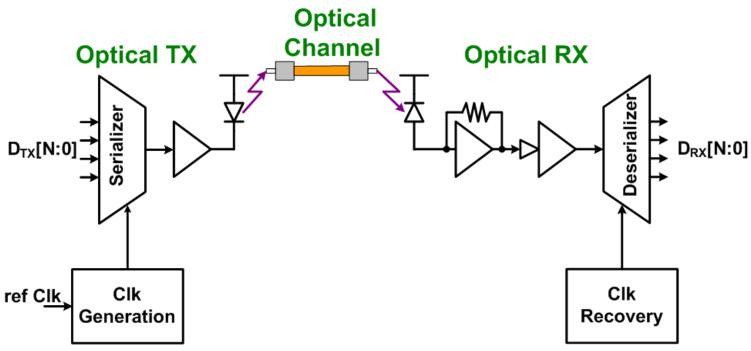
Link with Equalization



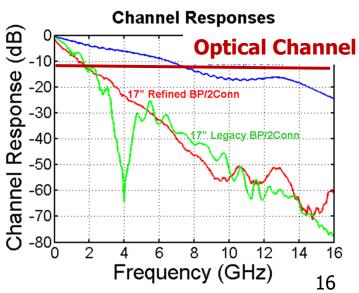
Channel Performance Impact



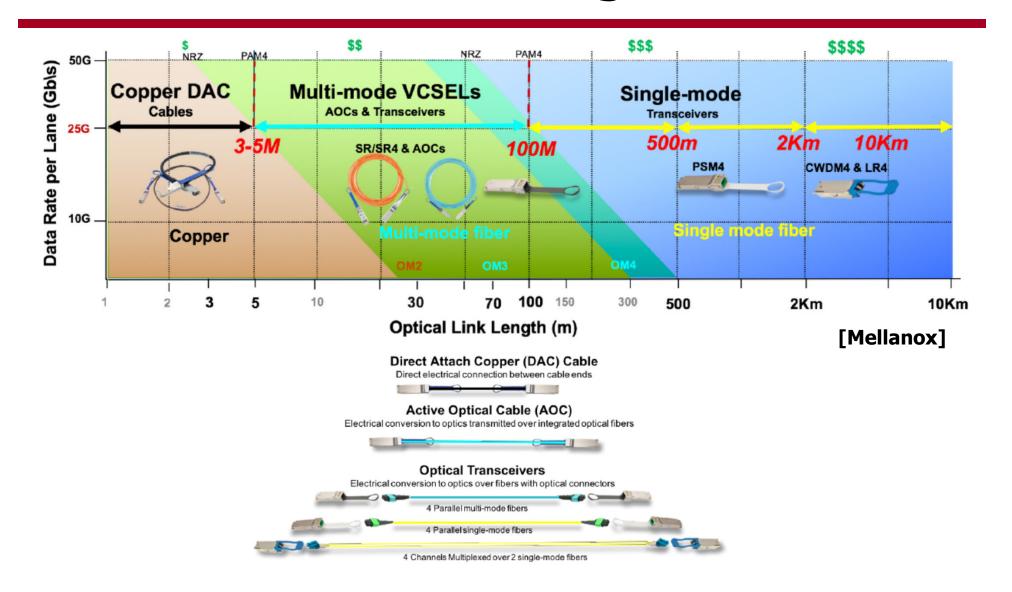
High-Speed Optical Link System



- Optical interconnects remove many channel limitations
 - Reduced complexity and power consumption
 - Potential for high information density with wavelength-division multiplexing (WDM)

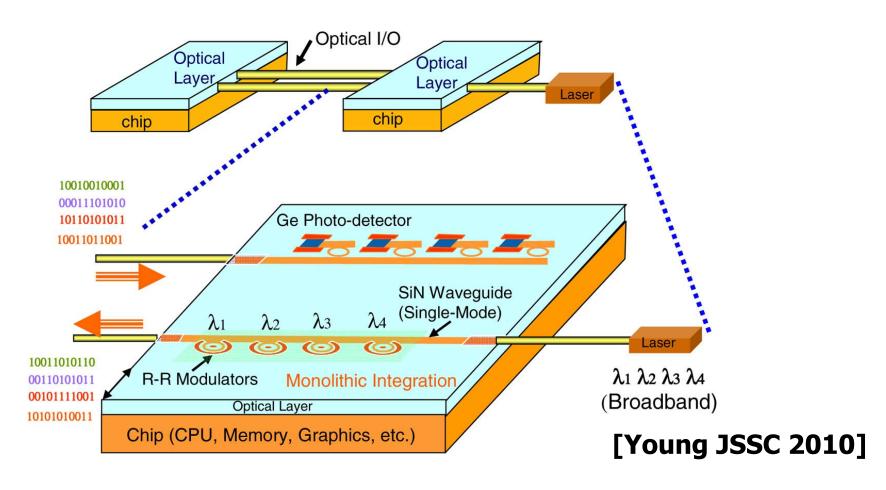


Data Center Link Length



Maximum reach scales inversely with data rate

Wavelength-Division Multiplexing



 WDM allows for multiple high-bandwidth (10+Gb/s) signals to be packed onto one optical channel

Optical Interconnects

- Electrical Channel Issues
- Optical Channel
- Optical Transmitter Technology
- Optical Receiver Technology
- Optical Integration Approaches

Optical Channels

- Short distance optical I/O channels are typically either waveguide (fiber)-based or free-space
- Optical channel advantages
 - Much lower loss
 - Lower cross-talk
 - Smaller waveguides relative to electrical traces
 - Potential for multiple data channels on single fiber via WDM

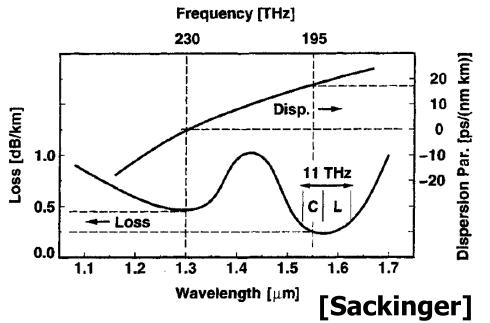
Waveguide (Fiber)-Based Optical Links

- Optical fiber loss is specified in dB/km
 - Single-Mode Fiber loss
 ~0.25dB/km at 1550nm
 - RF coaxial cable loss ~100dB/km at 10GHz
- Frequency dependent loss is very small
 - <0.5dB/km over a bandwidth>10THz
- Bandwidth may be limited by dispersion (pulse-spreading)
 - Important to limit laser linewidth for long distances (>1km)

Optical Fiber Cross-Section

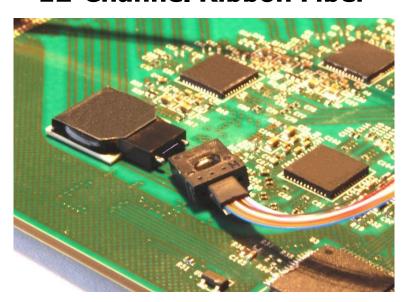


Single-Mode Fiber Loss & Dispersion



Inter-Chip Waveguide Examples

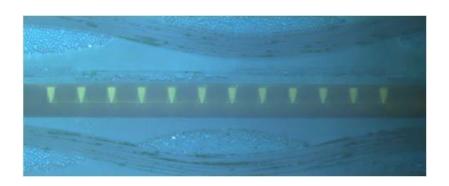
12-Channel Ribbon Fiber



[Reflex Photonics]

12 channels at a 250 μ m pitch 10Gb/s mod. \rightarrow 40Gb/s/mm

Optical Polymer Waveguide in PCB

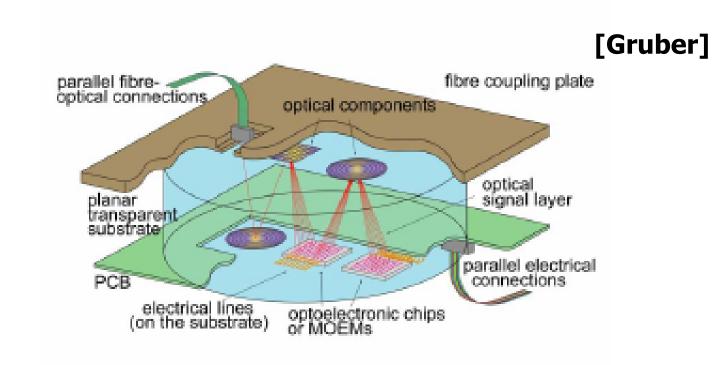


[Immonen 2009]

<100 μ m channel pitch possible 10Gb/s mod. \rightarrow 100+Gb/s/mm

Typical differential electrical strip lines are at ~500μm pitch

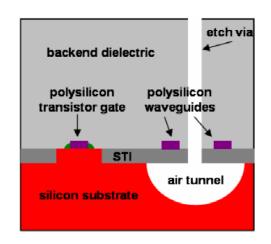
Free-Space Optical Links

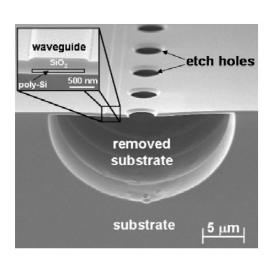


- Free-space (air or glass) interconnect systems have also been proposed
- Optical imaging system routes light chip-to-chip

CMOS Waveguides – Bulk CMOS

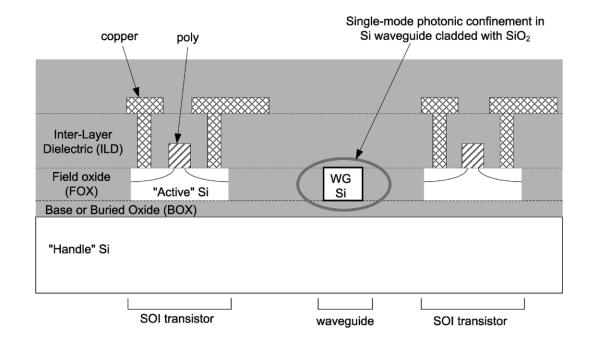
- Waveguides can be made in a bulk process with a polysilicon core surrounded by an SiO2 cladding
- However, thin STI layer means a significant portion of the optical mode will leak into the Si substrate, causing significant loss (1000dB/cm)
- Significant post-processing is required for reasonable loss (10dB/cm) waveguides in a bulk process





CMOS Waveguides – SOI

- SOI processes have thicker buried oxide layers to sufficiently confine the optical mode
- Allows for low-loss waveguides

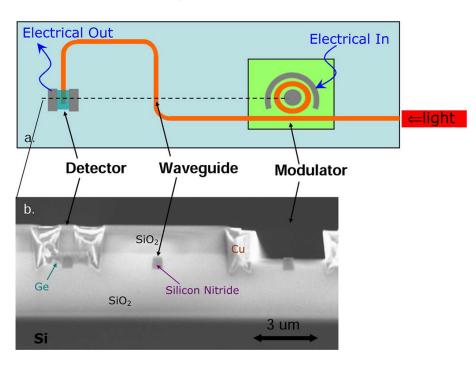


[Narasimha JSSC 2007]

CMOS Waveguides – Back-End Processing

- Waveguides & optical devices can be fabricated above metallization
- Reduces active area consumption
- Allows for independent optimization of transistor and optical device processes

[Young JSSC 2010]



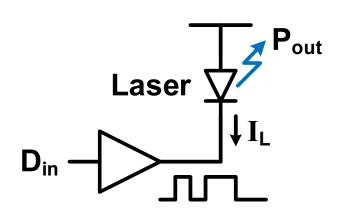
Optical Interconnects

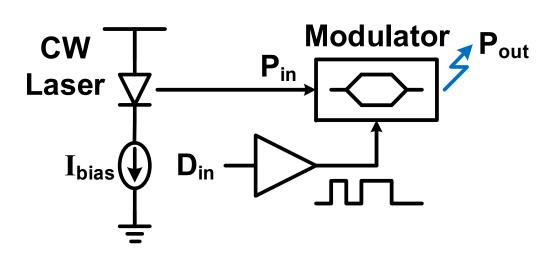
- Electrical Channel Issues
- Optical Channel
- Optical Transmitter Technology
- Optical Receiver Technology
- Optical Integration Approaches

Optical Modulation Techniques

Direct Modulation

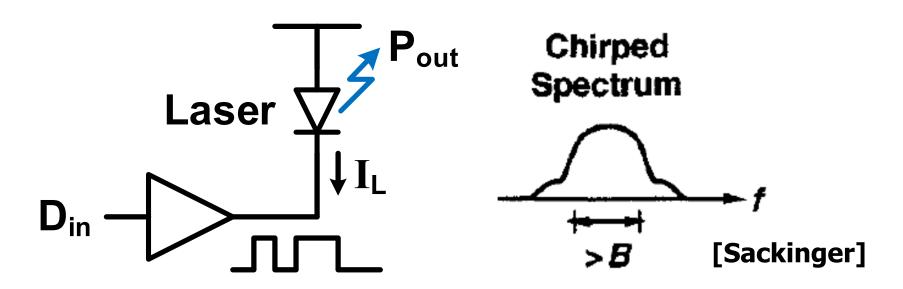
External Modulation





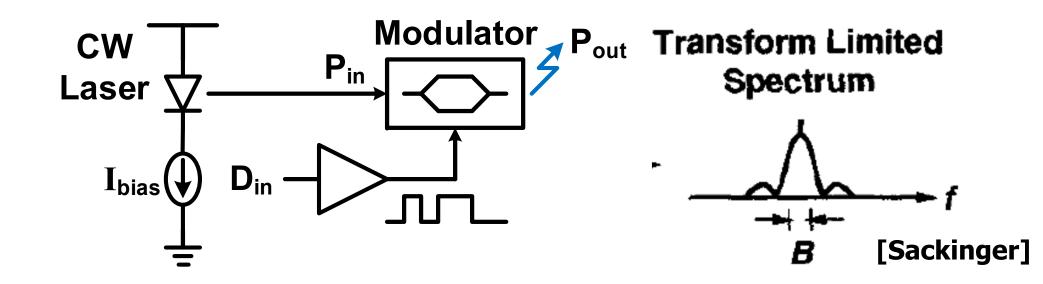
- Two modulation techniques
 - Direct modulation of laser
 - External modulation of continuous-wave (CW) "DC" laser with absorptive or refractive modulators

Directly Modulated Laser



- Directly modulating laser output power
- Simplest approach
- Introduces laser "chirp", which is unwanted frequency (wavelength) modulation
- This chirp causes unwanted pulse dispersion when passed through a long fiber

Externally Modulated Laser



- External modulation of continuous-wave (CW)
 "DC" laser with absorptive or refractive modulators
 - Adds an extra component
 - Doesn't add chirp, and allows for a transform limited spectrum

Optical Sources for Chip-to-Chip Links

 Vertical-Cavity Surface-Emitting Laser (VCSEL)

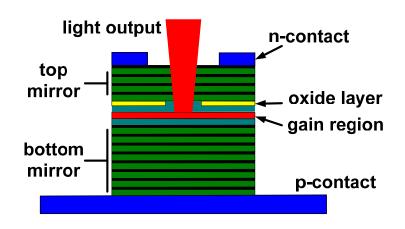
Electro-Absorption Modulator (EAM)

Ring-Resonator Modulator (RRM)

Mach-Zehnder Modulator (MZM)

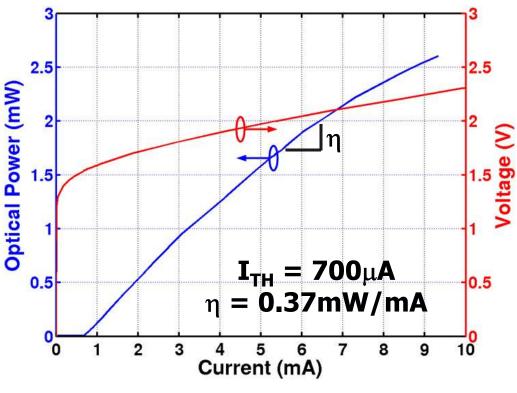
Vertical-Cavity Surface-Emitting Laser (VCSEL)

VCSEL Cross-Section



- VCSEL emits light perpendicular from top (or bottom) surface
- Important to always operate VCSEL above threshold current, I_{TH}, to prevent "turn-on delay" which results in ISI
- Operate at finite extinction ratio (P₁/P₀)

VCSEL L-I-V Curves

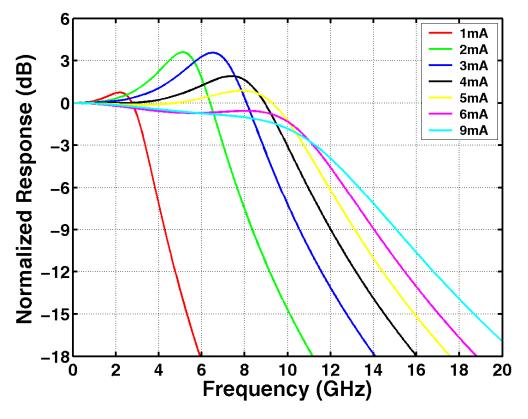


$$P_o = \eta (I - I_{TH})$$

Slope Efficiency
$$\eta = \frac{\Delta P}{\Delta I} \left(\frac{\mathbf{W}}{\mathbf{A}} \right)$$

VCSEL Bandwidth vs Reliability

10Gb/s VCSEL Frequency Response [1]



$$BW \propto \sqrt{I_{\rm avg} - I_{\rm TH}}$$

 Mean Time to Failure (MTTF) is inversely proportional to current density squared

$$MTTF = \frac{A}{j^2} e^{\left(\frac{E_A}{k}\right)\left(\frac{1}{T_j} - \frac{1}{373}\right)}$$
 [2]

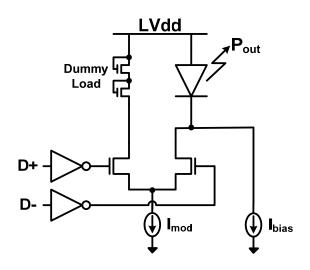
 Steep trade-off between bandwidth and reliability

$$MTTF \propto \frac{1}{BW^4}$$

- 1. D. Bossert *et al*, "Production of high-speed oxide confined VCSEL arrays for datacom applications," *Proceedings of SPIE*, 2002.
- 2. M. Teitelbaum and K. Goossen, "Reliability of Direct Mesa Flip-Chip Bonded VCSEL's," *LEOS*, 2004.

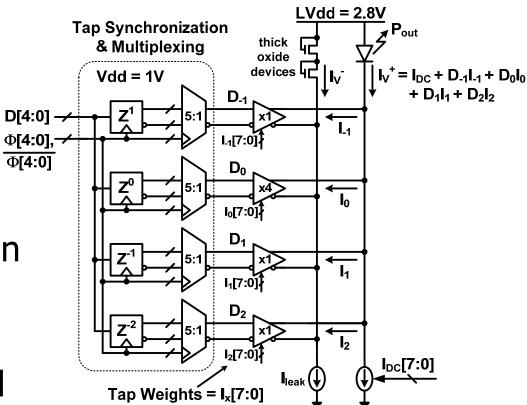
VCSEL Drivers

Current-Mode VCSEL Driver



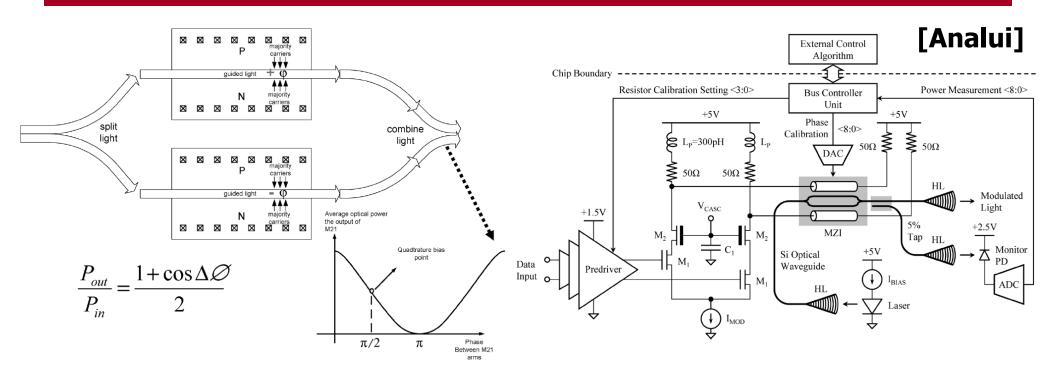
- Current-mode drivers often used due to linear L-I relationship
- Equalization can be added to extend VCSEL bandwidth for a given current density

VCSEL Driver w/ 4-tap FIR Equalization



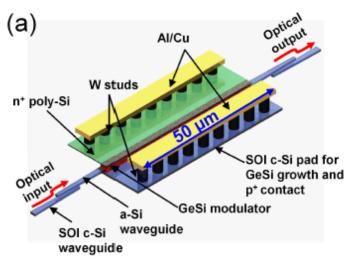
S. Palermo and M. Horowitz, "High-Speed Transmitters in 90nm CMOS for High-Density Optical Interconnects," *ESSCIRC*, 2006.

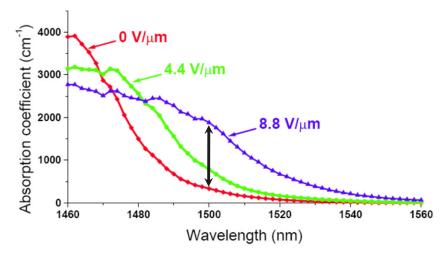
Mach-Zehnder Modulator (MZM)



- Refractive modulator which splits incoming light into two paths, induces a voltage-controlled phase shift in the two paths, and recombines the light in or out of phase
- Long device (several mm) requires driver to drive low-impedance transmission line at potentially high swing $(5V_{ppd})$
- While much higher power relative to RRM, they are less sensitive to temperature variations

Electro-Absorption Modulator (EAM)



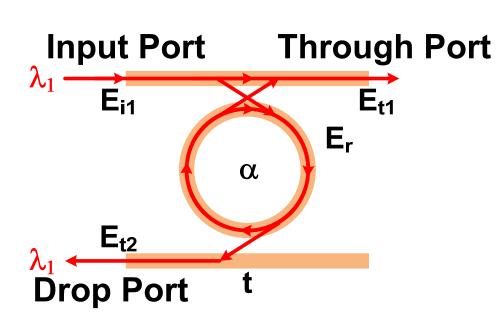


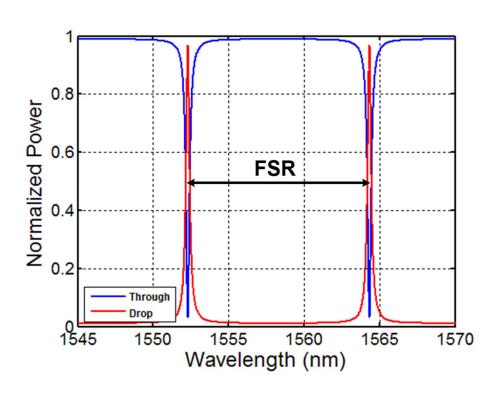
Waveguide EAM [Liu 2008]

[Helman JSTQE 2005]

- Electro-absorption modulators operate with voltage-dependent absorption of light passing through the device
- The device structure is a reverse-biased p-i-n diode
- The Franz-Keldysh effect describes how the effective bandgap of the semiconductor decreases with increasing electric field, shifting the absorption edge
- While this effect is weak, it can be enhanced with device structures with multiple quantum wells (MQW) through the quantum-confined Stark effect

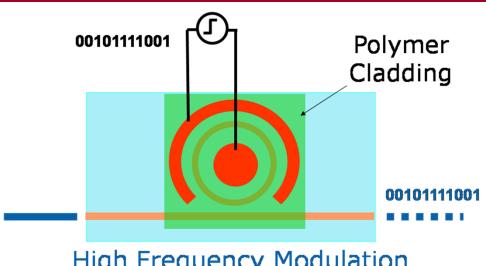
Ring Resonator Filter





- Ring resonators display a high-Q notch filter response at the through port and a band-pass response at the drop port
- This response repeats over a free spectral range (FSR)

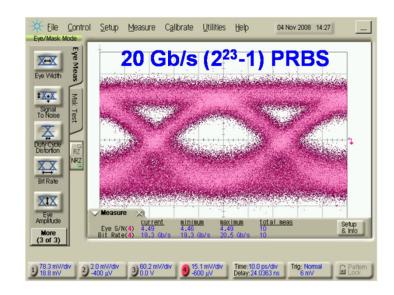
Ring-Resonator Modulator (RRM)



Normalized Transmission (dB) Voltage No Voltage ~8 dB **Applied Applied** Modulation Laser λ $\Delta \lambda / \Delta V = 5 \text{ pm/V}$ 1313.8 1314 1314.2 1314.6 1314.8 Wavelength (nm)

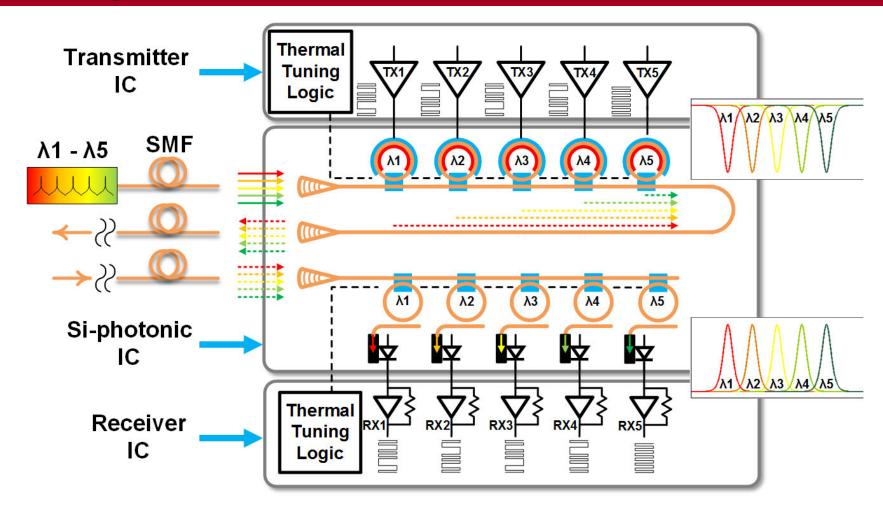
High Frequency Modulation

- Refractive devices which modulate by changing the interference light coupled into the ring with the waveguide light
- Devices are relatively small (ring diameters < 20µm) and can be treated as lumped capacitance loads (~10fF)



[Young ISSCC 2009]

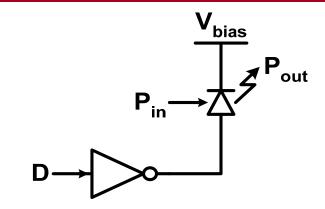
Wavelength Division Multiplexing w/ Ring Resonators



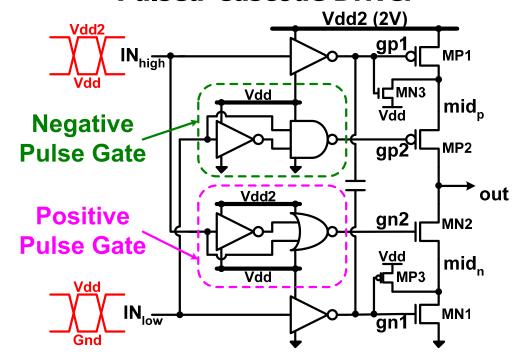
- Ring resonators can act as both modulators and add/drop filters to steer light to receivers or switch light to different waveguides
- Potential to pack >100 waveguides, each modulated at more than 10Gb/s on a single on-chip waveguide

CMOS Modulator Driver

- Simple CMOS-style voltage-mode drivers can drive EAM and RRM due to their small size
- Device may require swing higher than nominal CMOS supply
 - Pulsed-Cascode driver can reliably provide swing of 2xVdd (or 4xVdd) at up to 2FO4 data rate



Pulsed-Cascode Driver



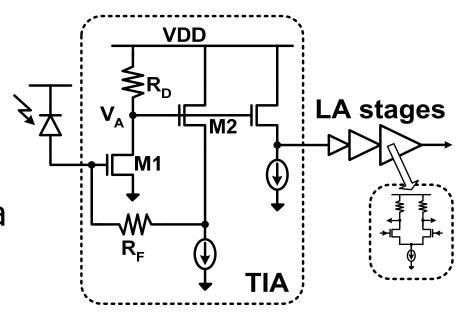
S. Palermo and M. Horowitz, "High-Speed Transmitters in 90nm CMOS for High-Density Optical Interconnects," *ESSCIRC*, 2006. 40

Optical Interconnects

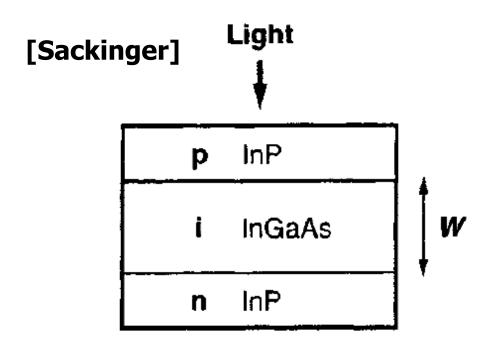
- Electrical Channel Issues
- Optical Channel
- Optical Transmitter Technology
- Optical Receiver Technology
- Optical Integration Approaches

Optical Receiver Technology

- Photodetectors convert optical power into current
 - p-i-n photodiodes
 - Integrated metal-semiconductormetal photodetector
- Electrical amplifiers then convert the photocurrent into a voltage signal
 - Transimpedance amplifiers
 - Limiting amplifiers
 - Integrating optical receiver



p-i-n Photodiode



Responsivity:

$$\rho = \frac{I}{P_{opt}} = \frac{\eta_{pd} \lambda q}{hc} = 8 \times 10^5 (\eta_{pd} \lambda) \text{ (mA/mW)}$$

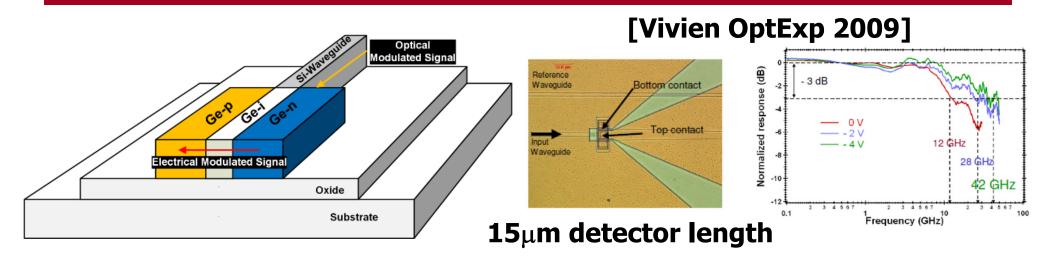
Quantum Efficiency: $\eta_{pd} = 1 - e^{-\alpha W}$

Transit-Time Limited Bandwidth:

$$f_{3dBPD} = \frac{2.4}{2\pi\tau_{tr}} = \frac{0.45v_{sat}}{W}$$

- Normally incident light absorbed in intrinsic region and generates carriers
- Trade-off between capacitance and transit-time
- Typical capacitance between 100-300fF

Waveguide p-i-n Photodetector



- A waveguide p-i-n photodetector structure allows this efficiency-speed trade-off to be broken
- The light travels horizontally down the intrinsic region and the electric field is formed orthogonal
- Allows for both a thin i-region for short transit times and a sufficiently long i-region for high quantum efficiency

Optical Interconnects

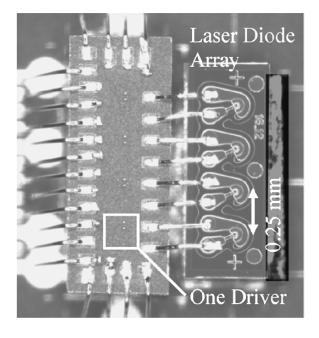
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Optical Integration Approaches

- Efficient cost-effective optical integration approaches are necessary for optical interconnects to realize their potential for improved power efficiency at higher data rates
- Hybrid integration
 - Optical devices fabricated on a separate substrate
- Integrated CMOS photonics
 - Optical devices part of CMOS chip

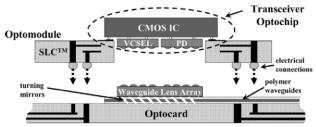
Hybrid Integration

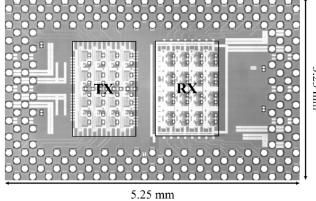
[Kromer]



Wirebonding

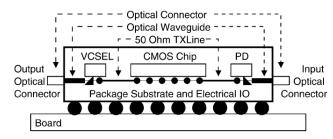
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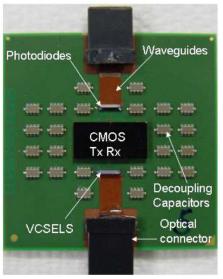




Flip-Chip Bonding

[Mohammed]



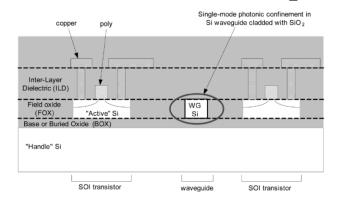


Short In-Package Traces

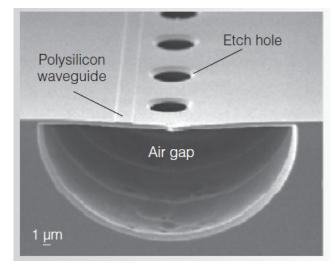
Integrated CMOS Photonics

SOI CMOS Process

[Analui]



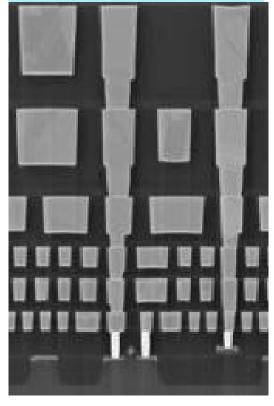
Bulk CMOS Process

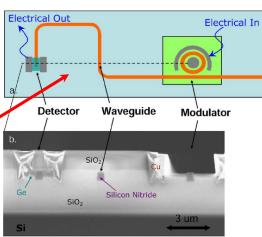


[Batten]



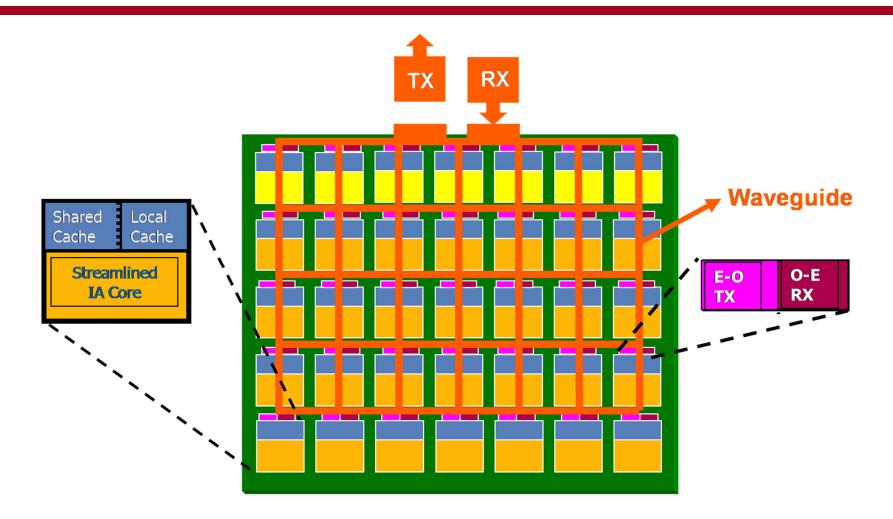
Optical Layer





[Young]

Future Photonic CMOS Chip



 Unified optical interconnect for on-chip core-to-core and offchip processor-to-processor and processor-to-memory

Next Time

- Optical Channels
 - Sackinger Chapter 2